

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> (Ω)	I <sub>D</sub> (A)
60V	0.08 @ V <sub>GS</sub> = 10V	5.3
	0.15 @ V <sub>GS</sub> = 4.5V	2.8

## Description and Applications

This MOSFET features a unique structure combining the benefits of low on-resistance and fast switching, making it ideal for high-efficiency power management applications.

- DC-DC converters
- Power management functions
- Disconnect switches
- Motor control

## Features and Benefits

- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](#) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([ZXMN6A08GQ](#))**

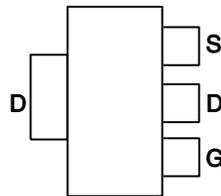
## Mechanical Data

- Package: SOT223 (Type DN)
- Package Material: Molded Plastic.  
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Solderable per MIL-STD-202, Method 208
- Weight: 0.112 grams (Approximate)

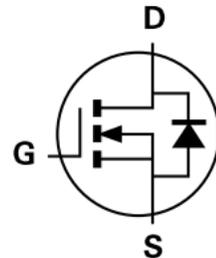
SOT223 (Type DN)



Top View



Pin Out - Top View



Equivalent Circuit

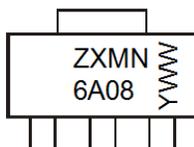
## Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
ZXMN6A08GTA	SOT223 (Type DN)	1,000	Tape & Reel
ZXMN6A08GTC	SOT223 (Type DN)	4,000	Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information

SOT223 (Type DN)



ZXMN6A08 = Product Type Marking Code  
 YWW = Date Code Marking  
 Y = Last Digit of Year (ex: 2 = 2022)  
 WW = Week Code (01 to 53)

## Maximum Ratings

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	60	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Continuous Drain Current ( $V_{GS} = 10V$ )	$I_D$	$T_A = +25^\circ C$ (Note 6)	5.3
		$T_A = +70^\circ C$ (Note 6)	4.2
		$T_A = +25^\circ C$ (Note 5)	3.8
Pulsed Drain Current (Note 7)	$I_{DM}$	20	A
Maximum Continuous Body Diode Forward Current (Note 6)	$I_S$	2.1	A
Pulsed Body Diode Forward Current (Note 7)	$I_{SM}$	20	A

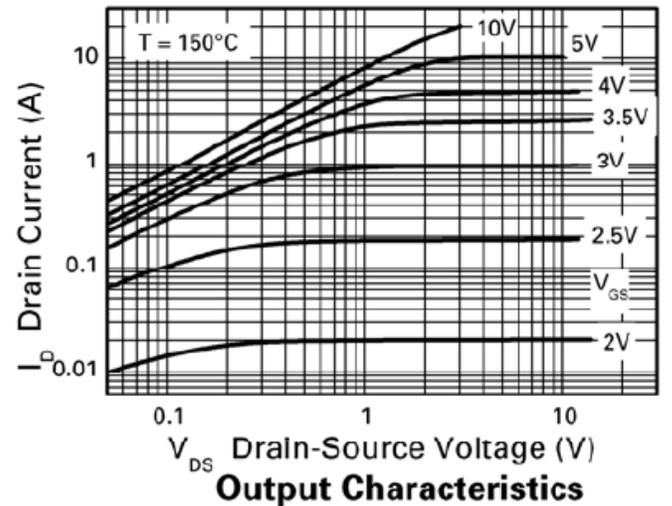
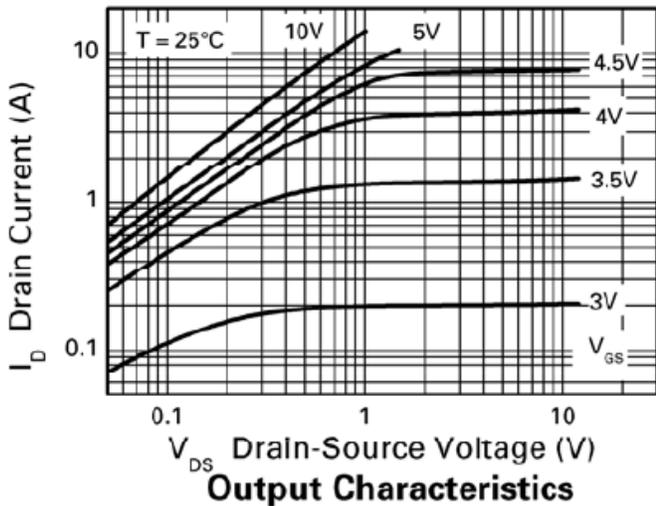
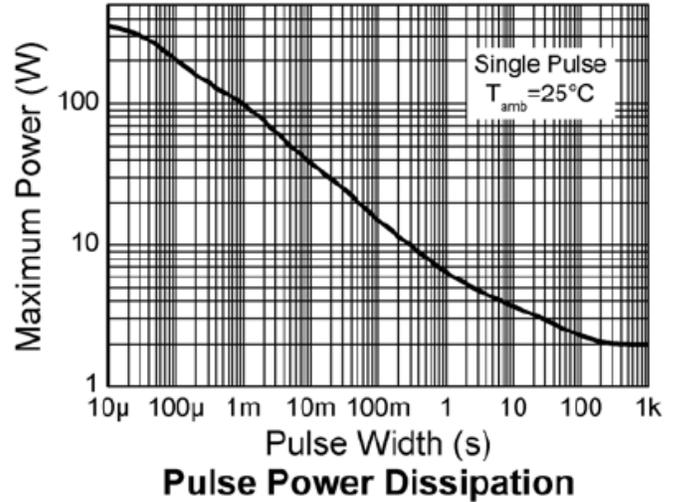
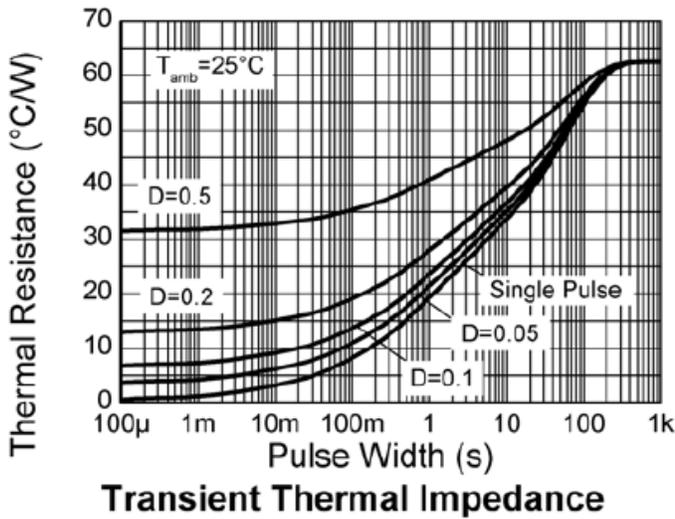
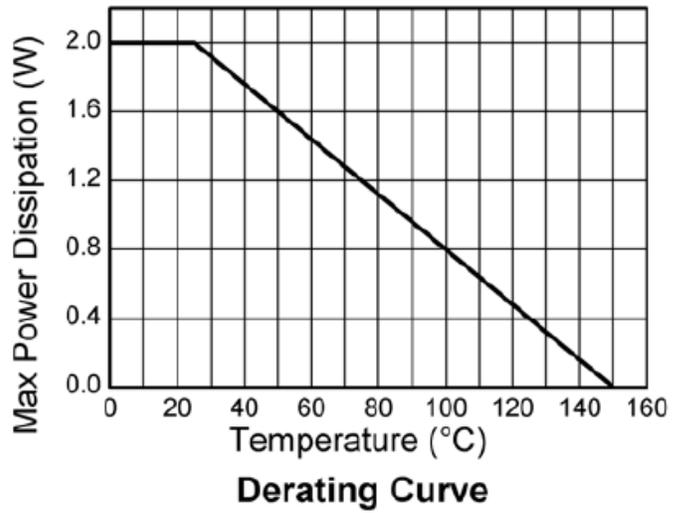
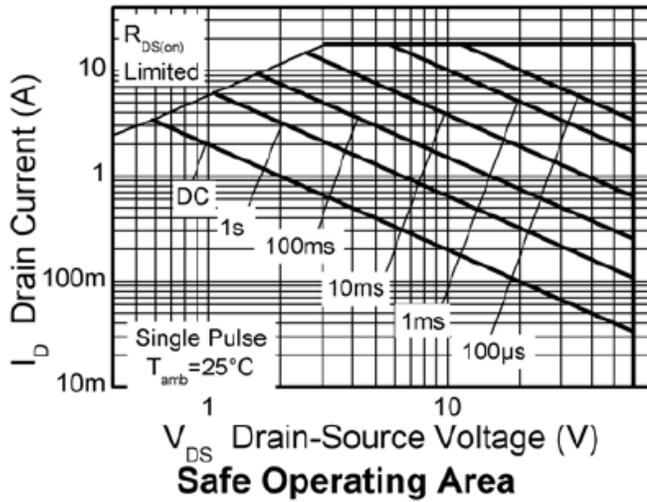
## Thermal Characteristics (@ $T_A = +25^\circ C$ , unless otherwise specified.)

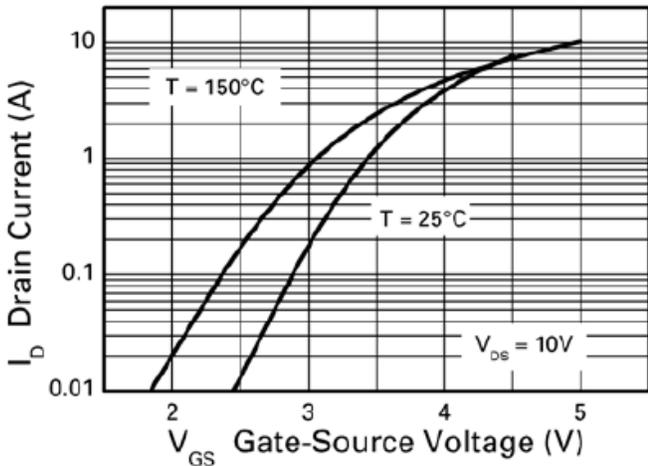
Characteristic	Symbol	Value	Units
Power Dissipation at $T_A = +25^\circ C$ (Note 5)	$P_D$	2	W
Linear Derating Factor		16	mW/ $^\circ C$
Junction to Ambient (Note 5)	$R_{\theta JA}$	62.5	$^\circ C/W$
Power Dissipation at $T_A = +25^\circ C$ (Note 6)	$P_D$	3.9	W
Linear Derating Factor		31	mW/ $^\circ C$
Junction to Ambient (Note 6)	$R_{\theta JA}$	32	$^\circ C/W$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ C$

## Electrical Characteristics (@ $T_A = +25^\circ C$ , unless otherwise specified.)

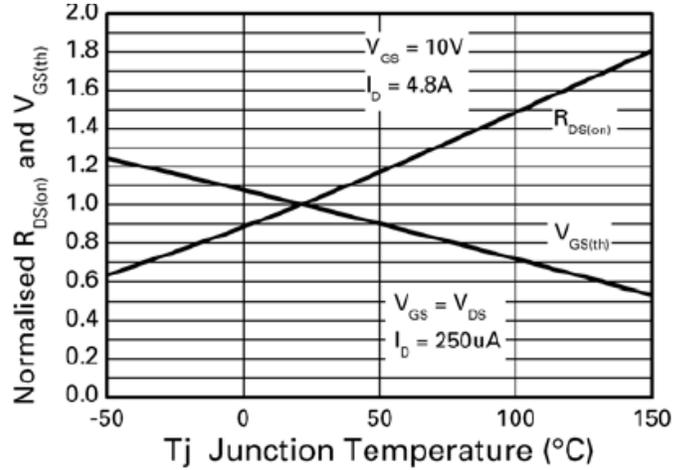
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	60	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	0.5	$\mu A$	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	$I_{GSS}$	—	—	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	1	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-State Resistance	$R_{DS(on)}$	—	0.06	0.08	$\Omega$	$V_{GS} = 10V, I_D = 4.8A$
		—	0.08	0.15	$\Omega$	$V_{GS} = 4.5V, I_D = 4.2A$
Forward Transconductance	$g_{fs}$	—	6.6	—	S	$V_{DS} = 15V, I_D = 4.8A$
Diode Forward Voltage	$V_{SD}$	—	0.88	1.2	V	$T_J = +25^\circ C, I_S = 4A, V_{GS} = 0V$
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	$C_{iss}$	—	459	—	pF	$V_{DS} = 40V, V_{GS} = 0V, f = 1MHz$
Output Capacitance	$C_{oss}$	—	44.2	—	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	24.1	—	pF	
Total Gate Charge ( $V_{GS} = 5V$ )	$Q_g$	—	4.0	—	nC	$V_{DS} = 30V, I_D = 1.4A$
Total Gate Charge ( $V_{GS} = 10V$ )	$Q_g$	—	5.8	—	nC	
Gate-Source Charge	$Q_{gs}$	—	1.4	—	nC	
Gate Drain Charge	$Q_{gd}$	—	1.9	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	2.6	—	ns	$V_{DD} = 30V, I_D = 1.5A, R_G = 6.0\Omega, V_{GS} = 10V$
Turn-On Rise Time	$t_R$	—	2.1	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	12.3	—	ns	
Turn-Off Fall Time	$t_F$	—	4.6	—	ns	
Reverse Recovery Time	$t_{RR}$	—	19.2	—	ns	$T_J = +25^\circ C, I_S = 1.4A, di/dt = 100A/\mu s$
Reverse Recovery Charge	$Q_{RR}$	—	30.3	—	nC	

- Notes:
- For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
  - For a device surface mounted on FR4 PCB measured at  $t \leq 10$  sec.
  - Repetitive rating - 25mm x 25mm FR4 PCB,  $D=0.02$ , pulse width 300 $\mu s$  - pulse width limited by maximum junction temperature.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

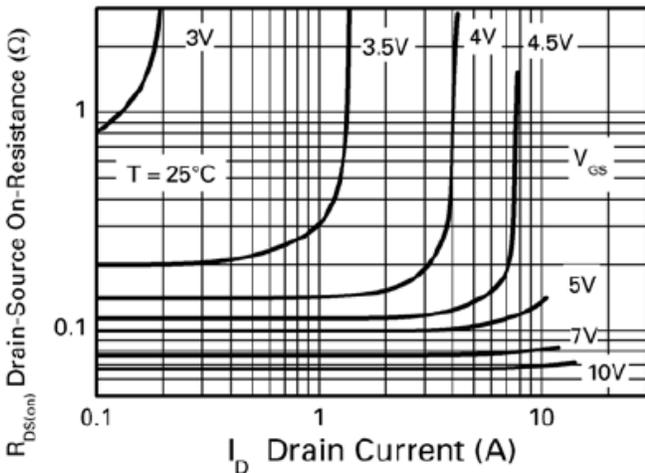




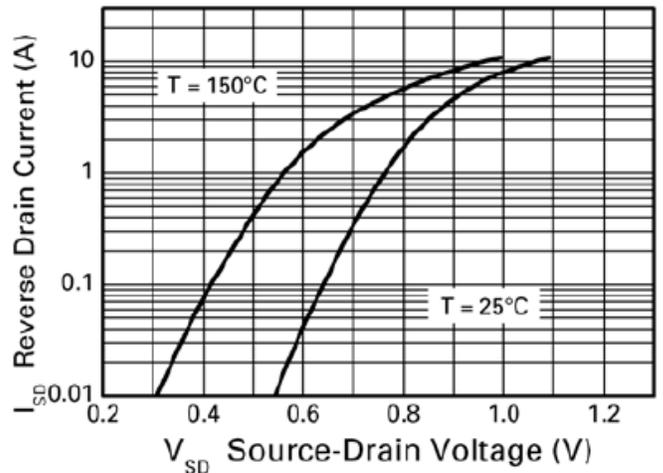
**Typical Transfer Characteristics**



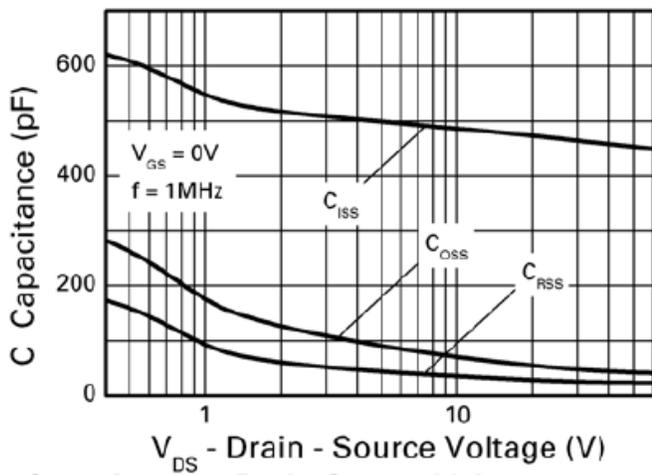
**Normalised Curves v Temperature**



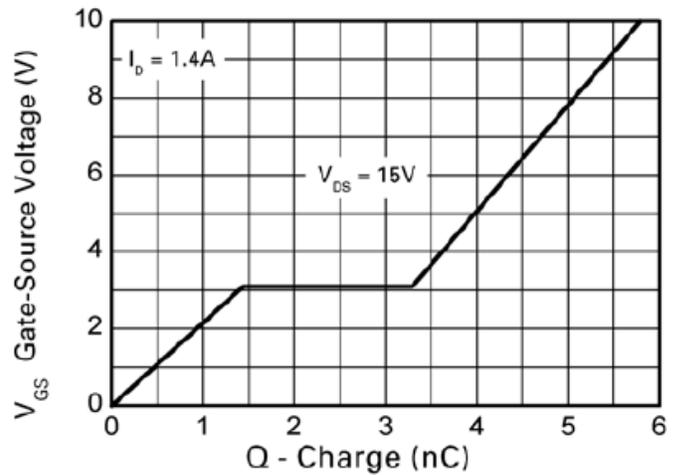
**On-Resistance v Drain Current**



**Source-Drain Diode Forward Voltage**

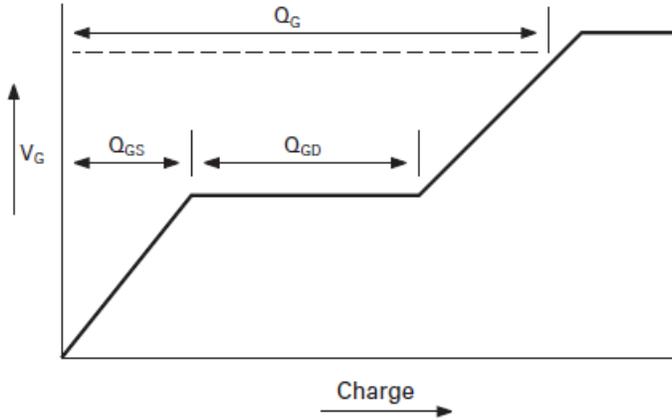


**Capacitance v Drain-Source Voltage**

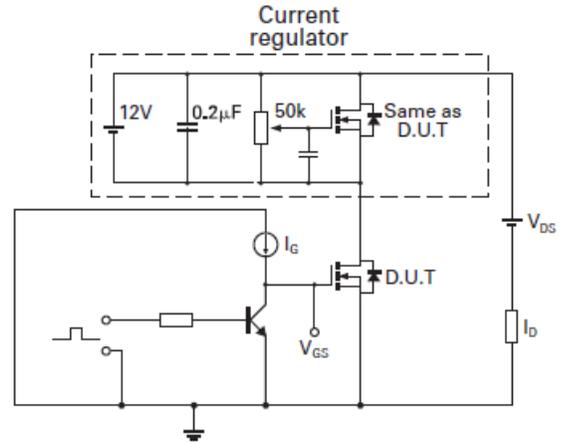


**Gate-Source Voltage v Gate Charge**

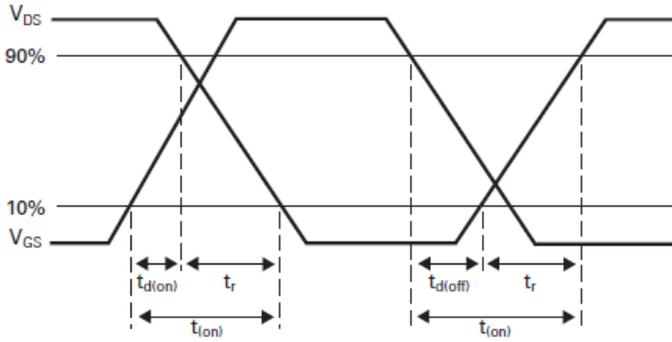
**Test Circuits**



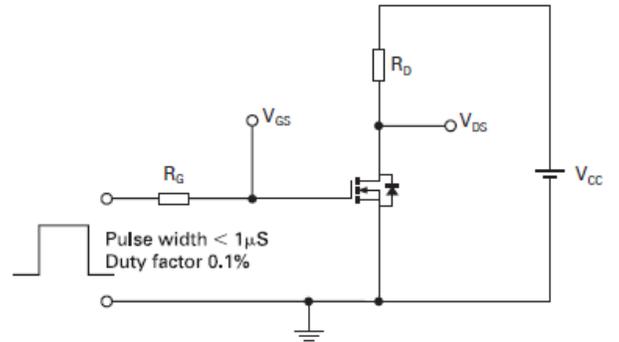
**Basic gate charge waveform**



**Gate charge test circuit**



**Switching time waveforms**

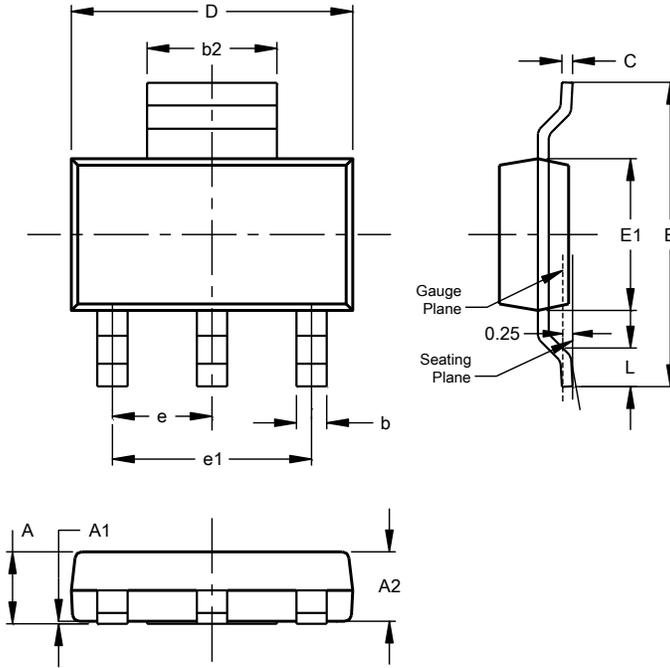


**Switching time test circuit**

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT223 (Type DN)**

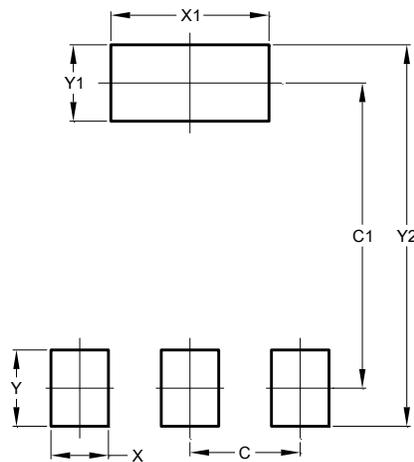


SOT223 (Type DN)			
Dim	Min	Max	Typ
A	--	1.70	--
A1	0.01	0.15	--
A2	1.50	1.68	1.60
b	0.60	0.80	0.70
b2	2.90	3.10	--
c	0.20	0.32	--
D	6.30	6.70	--
E	6.70	7.30	--
E1	3.30	3.70	--
e	--	--	2.30
e1	--	--	4.60
L	0.85	--	--
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT223 (Type DN)**



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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